

# Xia Guo

## List of Publications by Year in descending order

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Version: 2024-02-01

17  
papers

196  
citations

1307594

7  
h-index

1058476

14  
g-index

17  
all docs

17  
docs citations

17  
times ranked

326  
citing authors

#	ARTICLE	IF	CITATIONS
1	Carrier localization enhanced high responsivity in graphene/semiconductor photodetectors. , 2022, 1, 100006.		6
2	High-sensitivity graphene/Cu <sub>2</sub> O hybrid photodetectors based on photo-induced quantum capacitance. AIP Advances, 2022, 12, 045003.	1.3	1
3	Graphene/SrTiO <sub>3</sub> interface-based UV photodetectors with high responsivity*. Chinese Physics B, 2021, 30, 038502.	1.4	9
4	Graphene probe to explore the surface polarization in SrTiO <sub>3</sub> without damage. Applied Physics Letters, 2021, 119, .	3.3	3
5	Drop-casting CsPbBr <sub>3</sub> perovskite quantum dots as down-shifting layer enhancing the ultraviolet response of silicon avalanche photodiode. Applied Physics Letters, 2021, 119, .	3.3	8
6	Total dose test with $\hat{\Gamma}^3$ -ray for silicon single photon avalanche diodes*. Chinese Physics B, 2020, 29, 088501.	1.4	5
7	Interface-induced High Responsivity in Hybrid Graphene/GaAs Photodetector. Advanced Optical Materials, 2020, 8, 1901741.	7.3	31
8	Hybrid Graphene/Cu <sub>2</sub> O Quantum Dot Photodetectors with Ultrahigh Responsivity. Advanced Optical Materials, 2019, 7, 1900455.	7.3	30
9	In-Fiber Graphene-hBN Polarizer With Enhanced Performance and Bandwidth. IEEE Photonics Journal, 2019, 11, 1-8.	2.0	2
10	Coupled Equivalent Circuit for High-Speed Photodiodes. IEEE Electron Device Letters, 2019, 40, 1654-1657.	3.9	7
11	Graphene on Self-Assembled InGaN Quantum Dots Enabling Ultrahighly Sensitive Photodetectors. Advanced Optical Materials, 2019, 7, 1801792.	7.3	33
12	Effects of Interface States on Ge-On-SOI Photodiodes. IEEE Journal of the Electron Devices Society, 2019, 7, 7-12.	2.1	7
13	Vertical leakage induced current degradation and relevant traps with large lattice relaxation in AlGaIn/GaN heterostructures on Si. Applied Physics Letters, 2018, 112, 032104.	3.3	8
14	Hybrid graphene/unintentionally doped GaN ultraviolet photodetector with high responsivity and speed. Applied Physics Letters, 2018, 113, .	3.3	35
15	Graphene as current spreading layer on AlGaInP light emitting diodes. Journal of Applied Physics, 2018, 123, 175701.	2.5	2
16	Heat dissipation effect on modulation bandwidth of high-speed 850-nm VCSELs. Journal of Applied Physics, 2017, 121, .	2.5	6
17	Current Kink and Capacitance Frequency Dispersion in Silicon PIN Photodiodes. IEEE Journal of the Electron Devices Society, 2017, 5, 390-394.	2.1	3